

INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/587,414
	Filing Date	11/7/2006
	First Named Inventor	Vincent W. Leung
	Art Unit	2817
	Examiner Name	Nguyen, Khanh V.
Sheet 1 of 1	Attorney Docket Number	0321.72250

UNITED STATES PATENTS			
Examiner Initials*	Document No.	Dated	Inventor
/K.N./	2003/076171 20030076171	4/24/2003	Hwang

FOREIGN DOCUMENTS			
Examiner Initials*	Document No.	Dated	Inventor
/K.N./	WO 00/19327	4/6/2000	Actiontec Electronics, Inc.
/K.N./	WO 00/45507	8/3/2000	Nortel Networks Corp.
/K.N./	WO 03/005574	1/16/2003	Koninklijke Philips Electronics
/K.N./	WO 2004/070970	8/19/2004	Top Global USA, Inc.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), city and/or country where published.	T
/K.N./	1.	VINCENT LEUNG et al., "Digital-IF WCDMA Handset Transmitter IC in 0.25 μ m SiGe BiCMOS", Solid-State Circuits Conference 2004, Digest of Technical Papers, ISSCC, 2004, IEEE International, San Francisco, CA Feb. 15-19, 2004, Piscataway, NJ, IEEE, 2/15/2004, pp. 182-191.	
/K.N./	2.	SHINTARO SHINJO et al., "Low Quiescent Current SiGe HBT Driver Amplifier Having Self Base Bias Control Circuit", IEICE Transactions on Electronics, Vol. E85-C, No. 7, pp. 1404-11., 7/1/2002	Abstract only
/K.N./	3.	TIRDAD SOWLATI et al., "Bias Boosting Technique for a 1.9GHz Class AB RF Amplifier", Low Power Electronics and Design, 2000, Proceedings of the 2000 International Symposium on July 26-27, 2000, Piscataway, NJ.	